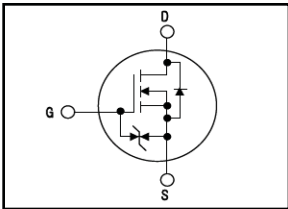
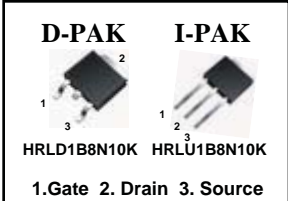


HRLD1B8N10K / HRLU1B8N10K

100V N-Channel Trench MOSFET

$BV_{DSS} = 100\text{ V}$
 $R_{DS(on) \text{ typ}} = 140\text{ m}\Omega$
 $I_D = 2.7\text{ A}$



FEATURES

- Originative New Design
- Superior Avalanche Rugged Technology
- Excellent Switching Characteristics
- Unrivalled Gate Charge : 11.5 nC (Typ.)
- Extended Safe Operating Area
- Lower $R_{DS(ON)}$: 140 m Ω (Typ.) @ $V_{GS}=10\text{V}$
- Lower $R_{DS(ON)}$: 185 m Ω (Typ.) @ $V_{GS}=4.5\text{V}$
- Built-in ESD Diode
- 100% Avalanche Tested

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	100	V
I_D	Drain Current – Continuous ($T_C = 25^\circ\text{C}$)	2.7	A
	Drain Current – Continuous ($T_C = 70^\circ\text{C}$)	2.1	A
I_{DM}	Drain Current – Pulsed (Note 1)	10.0	A
V_{GS}	Gate-Source Voltage	± 16	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	22	mJ
I_{AR}	Avalanche Current (Note 1)	2.7	A
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$)*	2.5	W
	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	33	W
		0.26	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Resistance Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	3.8	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient*	--	50	
$R_{\theta JA}$	Junction-to-Ambient	--	110	

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics $T_J=25\text{ }^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

On Characteristics

V_{GS}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.2	--	2.8	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\ \text{V}, I_D = 2.7\ \text{A}$	--	140	180	m Ω
		$V_{GS} = 4.5\ \text{V}, I_D = 2\ \text{A}$	--	185	240	m Ω

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\ \text{V}, I_D = 250\ \mu\text{A}$	100	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80\ \text{V}, V_{GS} = 0\ \text{V}$	--	--	1	μA
		$V_{DS} = 80\ \text{V}, T_J = 125\text{ }^\circ\text{C}$	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 16\ \text{V}, V_{DS} = 0\ \text{V}$	--	--	± 10	μA

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 30\ \text{V}, V_{GS} = 0\ \text{V},$ $f = 1.0\ \text{MHz}$	--	440	570	pF
C_{oss}	Output Capacitance		--	36	47	pF
C_{rss}	Reverse Transfer Capacitance		--	20	26	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Time	$V_{DS} = 50\ \text{V}, I_D = 2.7\ \text{A},$ $R_G = 25\ \Omega$	--	12	34	ns	
t_r	Turn-On Rise Time		--	16	42	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4,5)	--	55	120	ns
t_f	Turn-Off Fall Time			--	20	50	ns
Q_g	Total Gate Charge	$V_{DS} = 80\ \text{V}, I_D = 2.7\ \text{A},$ $V_{GS} = 10\ \text{V}$	--	11.5	15	nC	
Q_{gs}	Gate-Source Charge		(Note 4,5)	--	1.5	--	nC
Q_{gd}	Gate-Drain Charge			--	2.5	--	nC

Source-Drain Diode Maximum Ratings and Characteristics

I_S	Continuous Source-Drain Diode Forward Current	--	--	2.7	A	
I_{SM}	Pulsed Source-Drain Diode Forward Current	--	--	10		
V_{SD}	Source-Drain Diode Forward Voltage	$I_S = 2.7\ \text{A}, V_{GS} = 0\ \text{V}$	--	--	1.1	V
t_{rr}	Reverse Recovery Time	$I_S = 2\ \text{A}, V_{GS} = 0\ \text{V}$ $di_F/dt = 100\ \text{A}/\mu\text{s}$ (Note 4)	--	43	--	ns
Q_{rr}	Reverse Recovery Charge		--	73	--	nC

Notes ;

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L=1\text{mH}, I_{SD}\leq 5.5\text{A}, V_{DD}=25\text{V}, R_G=25\Omega,$ Starting $T_J=25\text{ }^\circ\text{C}$
3. $I_{SD}\leq 2.7\text{A}, di/dt\leq 200\text{A}/\mu\text{s}, V_{DD}\leq BV_{DSS},$ Starting $T_J=25\text{ }^\circ\text{C}$
4. Pulse Test : Pulse Width $\leq 300\mu\text{s},$ Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature

Typical Characteristics

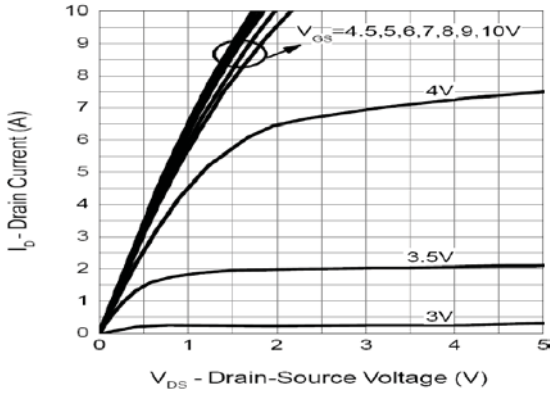


Figure 1. On Region Characteristics

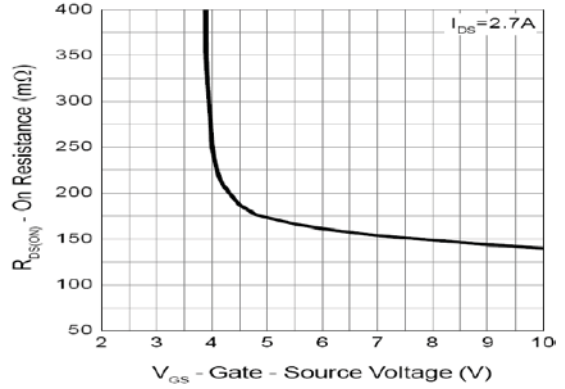


Figure 2. Gate-Source On Resistance

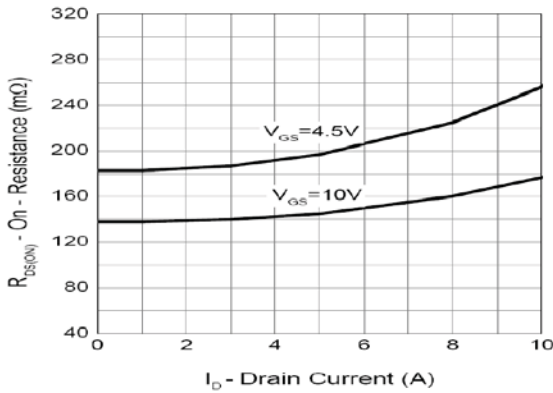


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

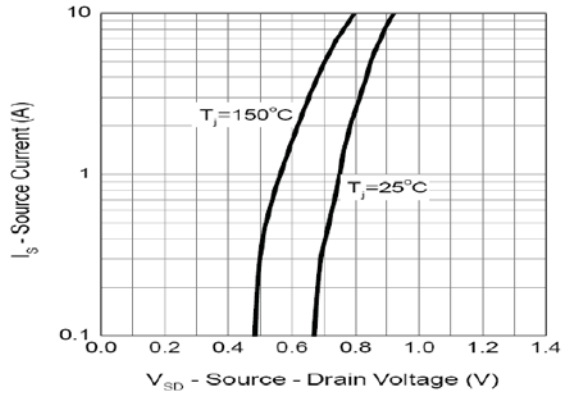


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

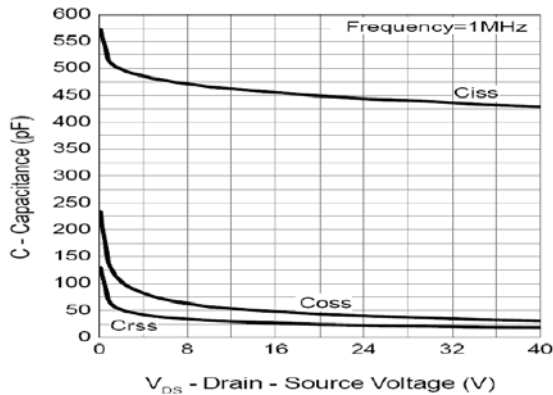


Figure 5. Capacitance Characteristics

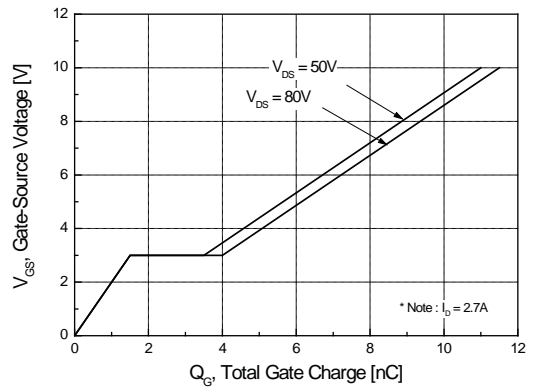


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

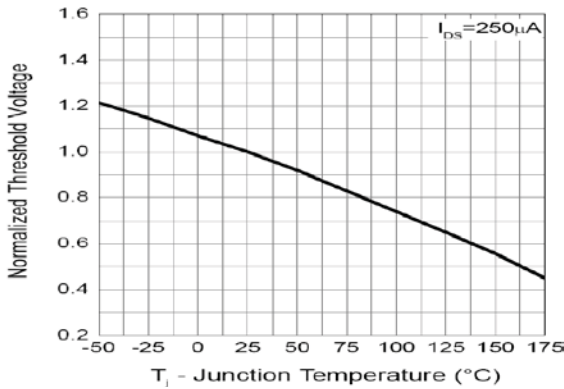


Figure 7. Gate Threshold Voltage vs Temperature

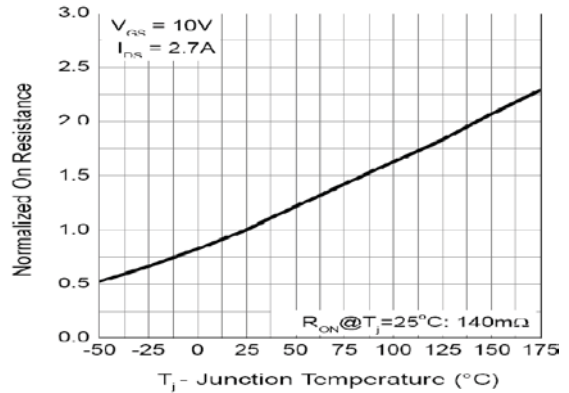


Figure 8. On-Resistance Variation vs Temperature

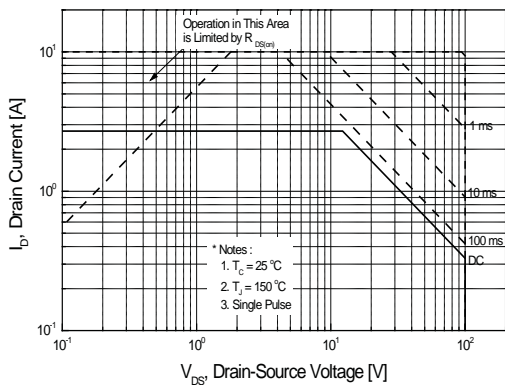


Figure 9. Maximum Safe Operating Area

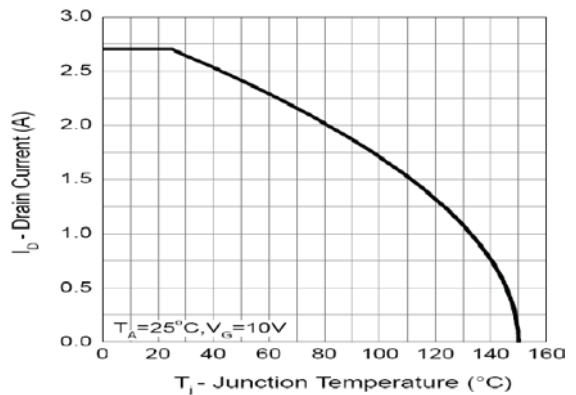


Figure 10. Maximum Drain Current vs Case Temperature

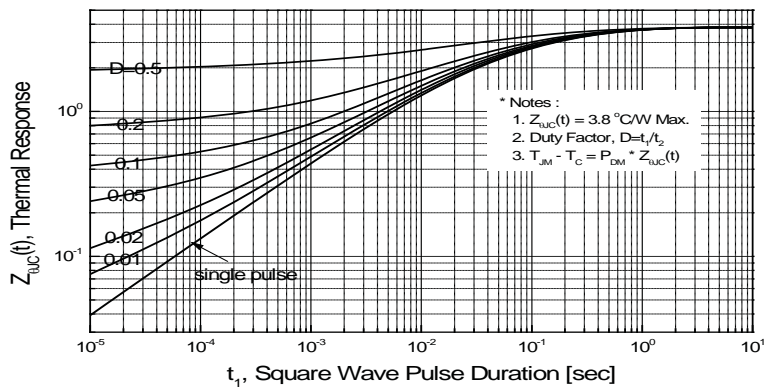


Figure 11. Transient Thermal Response Curve

Fig 12. Gate Charge Test Circuit & Waveform

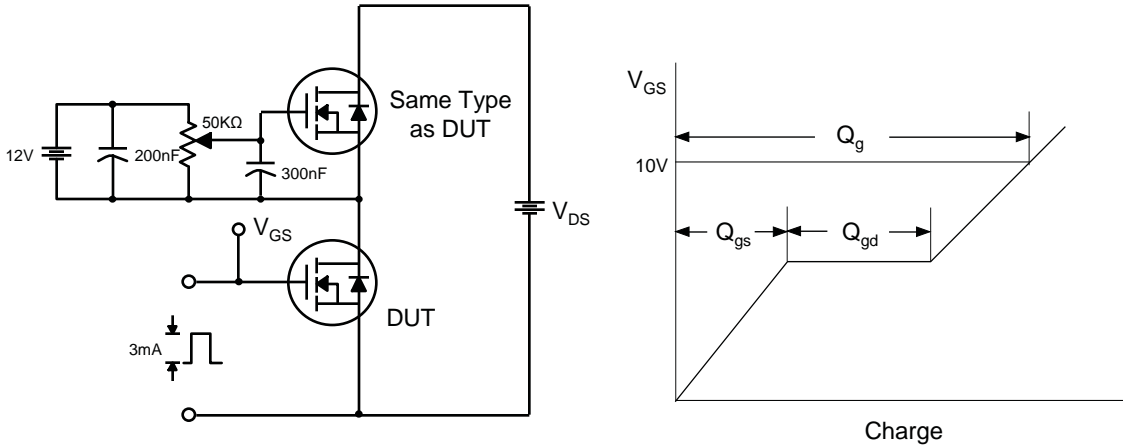


Fig 13. Resistive Switching Test Circuit & Waveforms

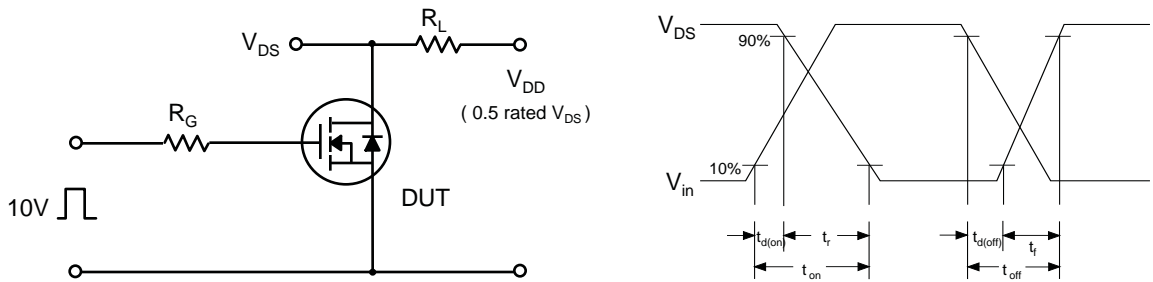


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

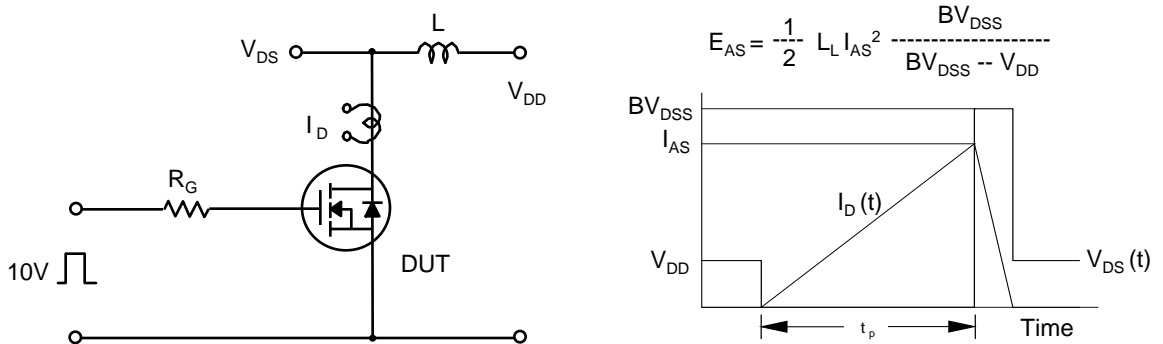
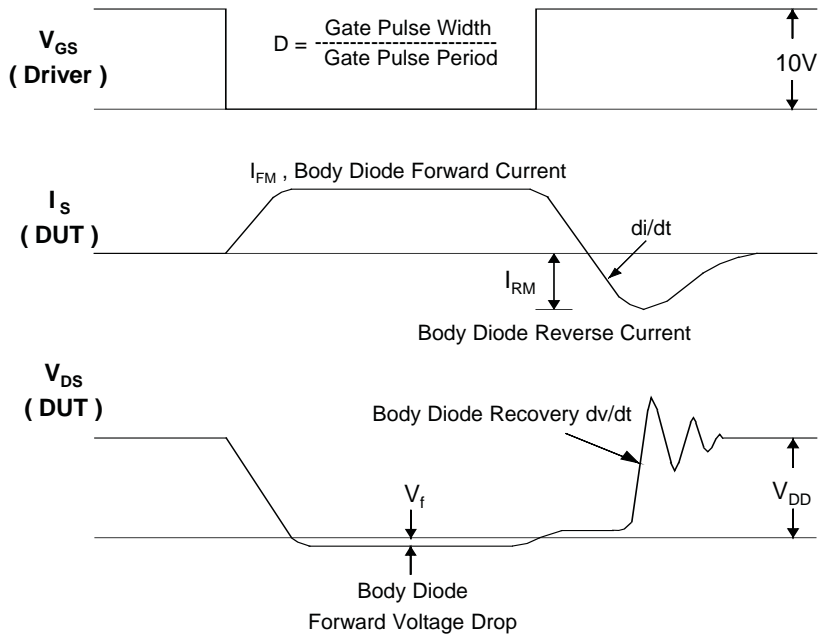
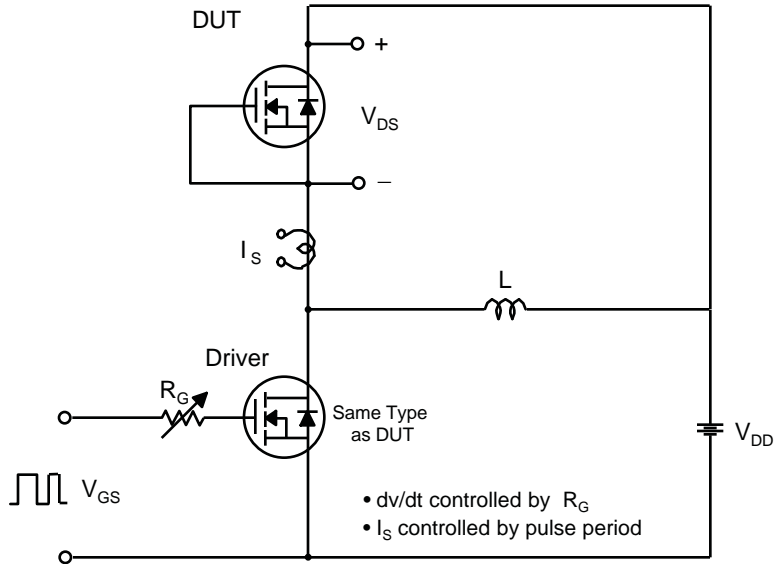
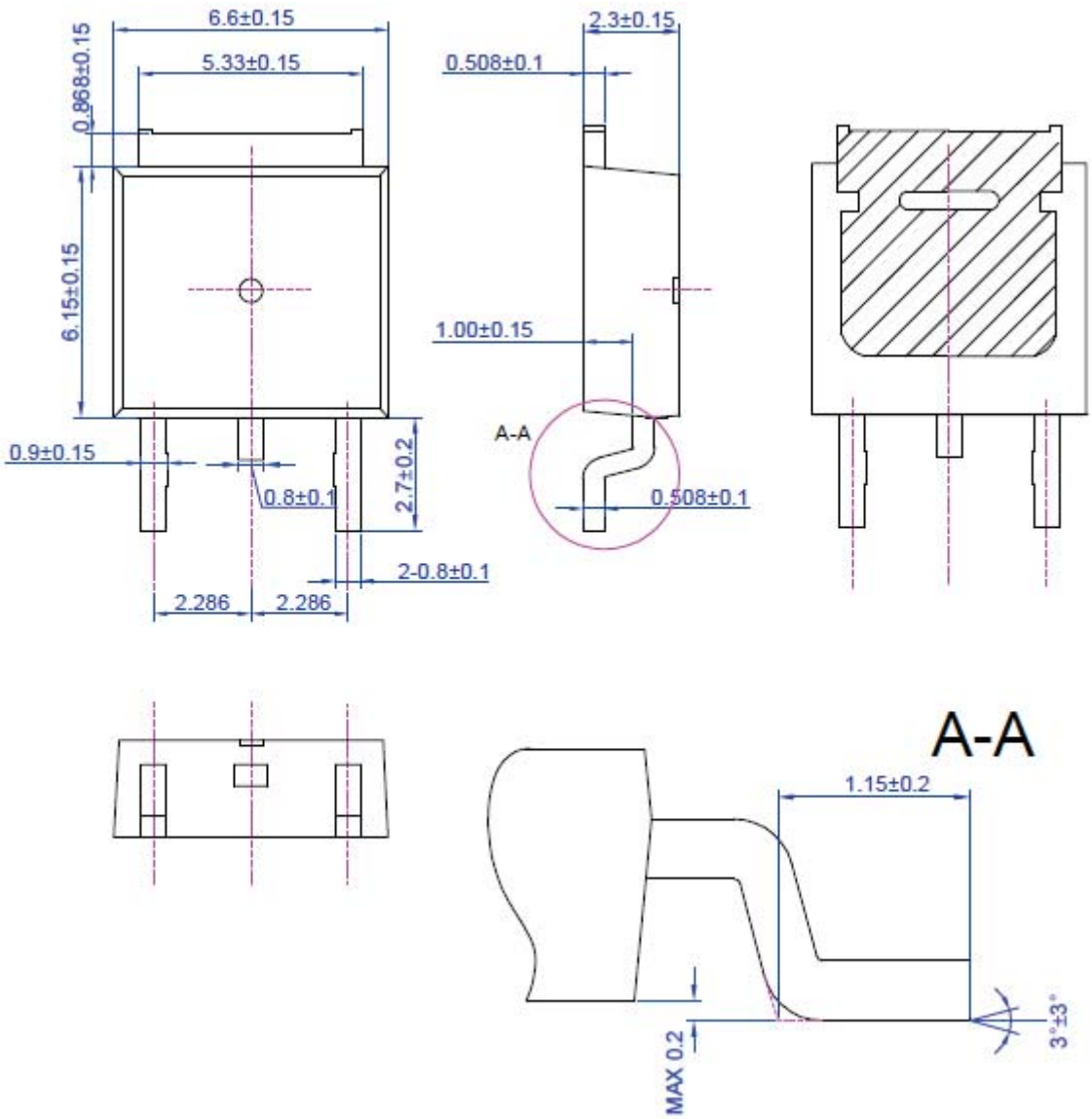


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



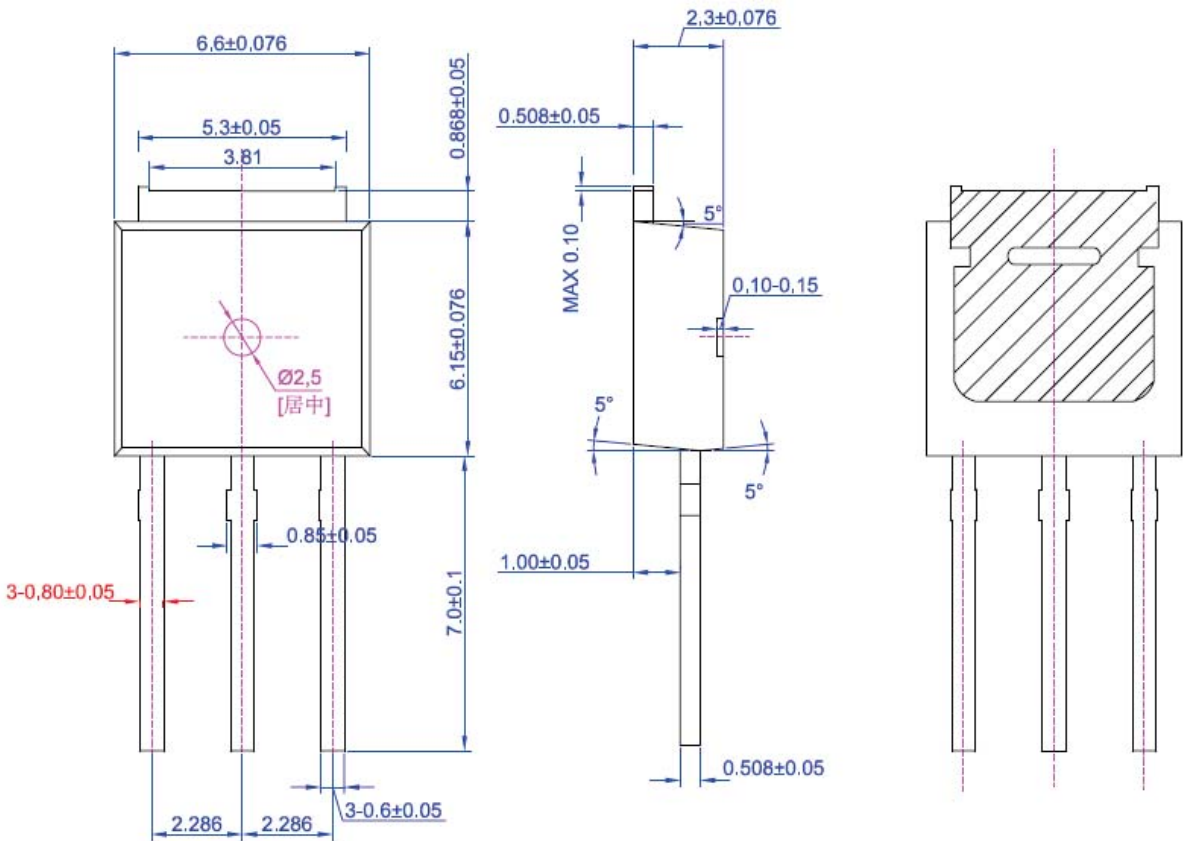
Package Dimension

TO-252
(Ass'y GZSM)



Package Dimension

TO-251
(Ass'y GZSM)



Package Dimension

TO-251
(Ass'y CLD)

